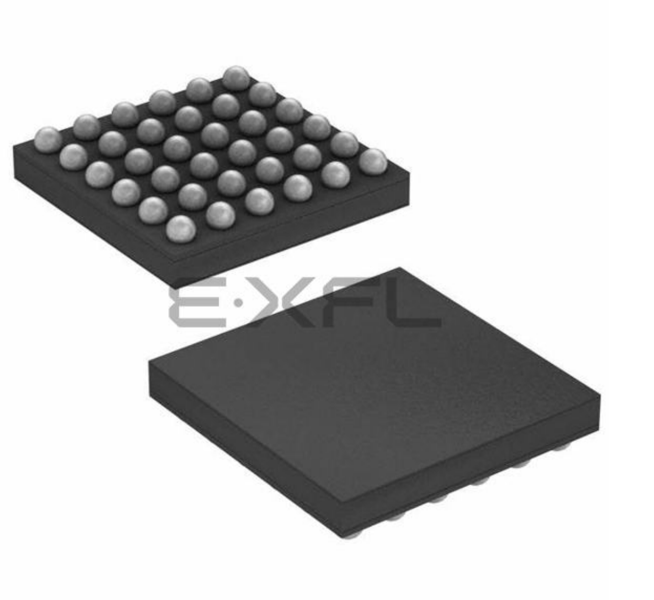

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What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "Embedded - Microcontrollers"

Details	
Product Status	Active
Core Processor	ARM® Cortex®-M0+
Core Size	32-Bit Single-Core
Speed	32MHz
Connectivity	I²C, IrDA, SPI, UART/USART
Peripherals	Brown-out Detect/Reset, DMA, I²S, POR, PWM, WDT
Number of I/O	29
Program Memory Size	64KB (64K x 8)
Program Memory Type	FLASH
EEPROM Size	2K x 8
RAM Size	8K x 8
Voltage - Supply (Vcc/Vdd)	1.8V ~ 3.6V
Data Converters	A/D 10x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	36-UFBGA, WLCSP
Supplier Device Package	36-WLCSP
Purchase URL	https://www.e-xfl.com/product-detail/stmicroelectronics/stm32l051t8y6tr

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Table 5. Functionalities depending on the working mode (from Run/active down to standby) (continued)(1)

IPs	Run/Active	Sleep	Low-power run	Low-power sleep	Stop		Standby	
						Wakeup capability		Wakeup capability
High Speed External (HSE)	O	O	O	O	--		--	
Low Speed Internal (LSI)	O	O	O	O	O		O	
Low Speed External (LSE)	O	O	O	O	O		O	
Multi-Speed Internal (MSI)	O	O	Y	Y	--		--	
Inter-Connect Controller	Y	Y	Y	Y	Y		--	
RTC	O	O	O	O	O	O	O	
RTC Tamper	O	O	O	O	O	O	O	O
Auto WakeUp (AWU)	O	O	O	O	O	O	O	O
USART	O	O	O	O	O(3)	O	--	
LPUART	O	O	O	O	O(3)	O	--	
SPI	O	O	O	O	--		--	
I2C	O	O	O	O	O(4)	O	--	
ADC	O	O	--	--	--		--	
Temperature sensor	O	O	O	O	O		--	
Comparators	O	O	O	O	O	O	--	
16-bit timers	O	O	O	O	--		--	
LPTIMER	O	O	O	O	O	O		
IWDG	O	O	O	O	O	O	O	O
WWDG	O	O	O	O	--		--	
SysTick Timer	O	O	O	O			--	
GPIOs	O	O	O	O	O	O		2 pins
Wakeup time to Run mode	0 µs	0.36 µs	3 µs	32 µs	3.5 µs		50 µs	

Nested vectored interrupt controller (NVIC)

The ultra-low-power STM32L051x6/8 embed a nested vectored interrupt controller able to handle up to 32 maskable interrupt channels and 4 priority levels.

The Cortex-M0+ processor closely integrates a configurable Nested Vectored Interrupt Controller (NVIC), to deliver industry-leading interrupt performance. The NVIC:

- includes a Non-Maskable Interrupt (NMI)
- provides zero jitter interrupt option
- provides four interrupt priority levels

The tight integration of the processor core and NVIC provides fast execution of Interrupt Service Routines (ISRs), dramatically reducing the interrupt latency. This is achieved through the hardware stacking of registers, and the ability to abandon and restart load-multiple and store-multiple operations. Interrupt handlers do not require any assembler wrapper code, removing any code overhead from the ISRs. Tail-chaining optimization also significantly reduces the overhead when switching from one ISR to another.

To optimize low-power designs, the NVIC integrates with the sleep modes, that include a deep sleep function that enables the entire device to enter rapidly stop or standby mode.

This hardware block provides flexible interrupt management features with minimal interrupt latency.

3.4 Reset and supply management

3.4.1 Power supply schemes

- V_{DD} = 1.65 to 3.6 V: external power supply for I/Os and the internal regulator. Provided externally through V_{DD} pins.
- V_{SSA}, V_{DDA} = 1.65 to 3.6 V: external analog power supplies for ADC reset blocks, RCs and PLL. V_{DDA} and V_{SSA} must be connected to V_{DD} and V_{SS}, respectively.

3.4.2 Power supply supervisor

The devices have an integrated ZEROPOWER power-on reset (POR)/power-down reset (PDR) that can be coupled with a brownout reset (BOR) circuitry.

Two versions are available:

- The version with BOR activated at power-on operates between 1.8 V and 3.6 V.
- The other version without BOR operates between 1.65 V and 3.6 V.

After the V_{DD} threshold is reached (1.65 V or 1.8 V depending on the BOR which is active or not at power-on), the option byte loading process starts, either to confirm or modify default thresholds, or to disable the BOR permanently: in this case, the VDD min value becomes 1.65 V (whatever the version, BOR active or not, at power-on).

When BOR is active at power-on, it ensures proper operation starting from 1.8 V whatever the power ramp-up phase before it reaches 1.8 V. When BOR is not active at power-up, the power ramp-up should guarantee that 1.65 V is reached on V_{DD} at least 1 ms after it exits the POR area.

Five BOR thresholds are available through option bytes, starting from 1.8 V to 3 V. To reduce the power consumption in Stop mode, it is possible to automatically switch off the

  - 32.768 kHz low-speed external crystal (LSE)
  - 37 kHz low-speed internal RC (LSI), also used to drive the independent watchdog. The LSI clock can be measured using the high-speed internal RC oscillator for greater precision.
- **RTC clock source**

  The LSI, LSE or HSE sources can be chosen to clock the RTC, whatever the system clock.
- **Startup clock**

  After reset, the microcontroller restarts by default with an internal 2 MHz clock (MSI). The prescaler ratio and clock source can be changed by the application program as soon as the code execution starts.
- **Clock security system (CSS)**

  This feature can be enabled by software. If an HSE clock failure occurs, the master clock is automatically switched to HSI and a software interrupt is generated if enabled.

  Another clock security system can be enabled, in case of failure of the LSE it provides an interrupt or wakeup event which is generated if enabled.
- **Clock-out capability (MCO: microcontroller clock output)**

  It outputs one of the internal clocks for external use by the application.

Several prescalers allow the configuration of the AHB frequency, each APB (APB1 and APB2) domains. The maximum frequency of the AHB and the APB domains is 32 MHz. See *Figure 2* for details on the clock tree.

To improve the accuracy of the temperature sensor measurement, each device is individually factory-calibrated by ST. The temperature sensor factory calibration data are stored by ST in the system memory area, accessible in read-only mode.

Table 7. Temperature sensor calibration values

Calibration value name	Description	Memory address
TSENSE_CAL1	TS ADC raw data acquired at temperature of 30 °C, V_{DDA}= 3 V	0x1FF8 007A - 0x1FF8 007B
TSENSE_CAL2	TS ADC raw data acquired at temperature of 130 °C V_{DDA}= 3 V	0x1FF8 007E - 0x1FF8 007F

3.12.1 Internal voltage reference (V_{REFINT})

The internal voltage reference (V_{REFINT}) provides a stable (bandgap) voltage output for the ADC and Comparators. V_{REFINT} is internally connected to the ADC_IN17 input channel. It enables accurate monitoring of the V_{DD} value (when no external voltage, V_{REF+}, is available for ADC). The precise voltage of V_{REFINT} is individually measured for each part by ST during production test and stored in the system memory area. It is accessible in read-only mode.

Table 8. Internal voltage reference measured values

Calibration value name	Description	Memory address
VREFINT_CAL	Raw data acquired at temperature of 25 °C V_{DDA} = 3 V	0x1FF8 0078 - 0x1FF8 0079

3.13 Ultra-low-power comparators and reference voltage

The STM32L051x6/8 embed two comparators sharing the same current bias and reference voltage. The reference voltage can be internal or external (coming from an I/O).

- One comparator with ultra low consumption
- One comparator with rail-to-rail inputs, fast or slow mode.
- The threshold can be one of the following:
  - External I/O pins
  - Internal reference voltage (V_{REFINT})
  - submultiple of Internal reference voltage(1/4, 1/2, 3/4) for the rail to rail comparator.

Both comparators can wake up the devices from Stop mode, and be combined into a window comparator.

The internal reference voltage is available externally via a low-power / low-current output buffer (driving current capability of 1 µA typical).

6 Electrical characteristics

6.1 Parameter conditions

Unless otherwise specified, all voltages are referenced to V_{SS}.

6.1.1 Minimum and maximum values

Unless otherwise specified the minimum and maximum values are guaranteed in the worst conditions of ambient temperature, supply voltage and frequencies by tests in production on 100% of the devices with an ambient temperature at T_A = 25 °C and T_A = $T_A$max (given by the selected temperature range).

Data based on characterization results, design simulation and/or technology characteristics are indicated in the table footnotes and are not tested in production. Based on characterization, the minimum and maximum values refer to sample tests and represent the mean value plus or minus three times the standard deviation (mean±3σ).

6.1.2 Typical values

Unless otherwise specified, typical data are based on T_A = 25 °C, V_{DD} = 3.6 V (for the 1.65 V ≤V_{DD} ≤3.6 V voltage range). They are given only as design guidelines and are not tested.

Typical ADC accuracy values are determined by characterization of a batch of samples from a standard diffusion lot over the full temperature range, where 95% of the devices have an error less than or equal to the value indicated (mean±2σ).

6.1.3 Typical curves

Unless otherwise specified, all typical curves are given only as design guidelines and are not tested.

6.1.4 Loading capacitor

The loading conditions used for pin parameter measurement are shown in *Figure 10*.

6.1.5 Pin input voltage

The input voltage measurement on a pin of the device is described in *Figure 11*.

Figure 10. Pin loading conditions

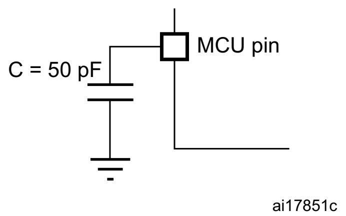
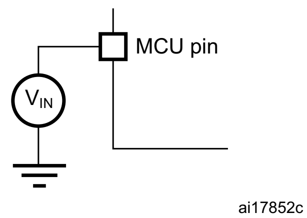


Figure 11. Pin input voltage



6.2 Absolute maximum ratings

Stresses above the absolute maximum ratings listed in *Table 20: Voltage characteristics*, *Table 21: Current characteristics*, and *Table 22: Thermal characteristics* may cause permanent damage to the device. These are stress ratings only and functional operation of the device at these conditions is not implied. Exposure to maximum rating conditions for extended periods may affect device reliability. Device mission profile (application conditions) is compliant with JEDEC JESD47 Qualification Standard. Extended mission profiles are available on demand.

Table 20. Voltage characteristics

Symbol	Definition	Min	Max	Unit
$V_{DD}–V_{SS}$	External main supply voltage (including V_{DDA}, V_{DDIO2}, V_{DD})(1)	–0.3	4.0	V
V_{IN}(2)	Input voltage on FT and FTf pins	V_{SS} –0.3	V_{DD}+4.0	
	Input voltage on TC pins	V_{SS} –0.3	4.0	
	Input voltage on BOOT0	V_{SS}	V_{DD} +4.0	
	Input voltage on any other pin	V_{SS} –0.3	4.0	
$\|\Delta V_{DD}\|$	Variations between different V_{DDx} power pins	-	50	mV
$\|V_{DDA}-V_{DDx}\|$	Variations between any V_{DDx} and V_{DDA} power pins(3)	-	300	
$\|\Delta V_{SS}\|$	Variations between all different ground pins	-	50	
$V_{REF+} –V_{DDA}$	Allowed voltage difference for $V_{REF+} > V_{DDA}$	-	0.4	V
$V_{ESD(HBM)}$	Electrostatic discharge voltage (human body model)	see *Section 6.3.11*		

1. All main power (V_{DD},V_{DDIO2}, V_{DDA}) and ground (V_{SS}, V_{SSA}) pins must always be connected to the external power supply, in the permitted range.
2. V_{IN} maximum must always be respected. Refer to *Table 21* for maximum allowed injected current values.
3. It is recommended to power V_{DD} and V_{DDA} from the same source. A maximum difference of 300 mV between V_{DD} and V_{DDA} can be tolerated during power-up and device operation. V_{DDIO2} is independent from V_{DD} and V_{DDA}: its value does not need to respect this rule.

6.3 Operating conditions

6.3.1 General operating conditions

Table 23. General operating conditions

Symbol	Parameter	Conditions	Min	Max	Unit
f_{HCLK}	Internal AHB clock frequency	-	0	32	MHz
f_{PCLK1}	Internal APB1 clock frequency	-	0	32	
f_{PCLK2}	Internal APB2 clock frequency	-	0	32	
V_{DD}	Standard operating voltage	BOR detector disabled	1.65	3.6	V
		BOR detector enabled, at power-on	1.8	3.6	
		BOR detector disabled, after power-on	1.65	3.6	
V_{DDA}	Analog operating voltage (all features)	Must be the same voltage as V_{DD} (1)	1.65	3.6	V
V_{DDIO2}	Standard operating voltage	-	1.65	3.6	V
V_{IN}	Input voltage on FT, FTf and RST pins(2)	$2.0\ V \le V_{DD} \le 3.6\ V$	-0.3	5.5	V
		$1.65\ V \le V_{DD} \le 2.0\ V$	-0.3	5.2	
	Input voltage on BOOT0 pin	-	0	5.5	
	Input voltage on TC pin	-	-0.3	V_{DD}+0.3	
P_D	Power dissipation at T_A = 85 °C (range 6) or T_A =105 °C (rage 7) (3)	TFBGA64 package	-	327	mW
		LQFP64 package	-	444	
		LQFP48 package	-	363	
		Standard WLCSP36 package	-	318	
		Thin WLCSP36 package	-	338	
		LQFP32 package	-	351	
		UFQFPN32	-	526	
	Power dissipation at T_A = 125 °C (range 3) (3)	TFBGA64 package	-	81	
		LQFP64 package	-	111	
		LQFP48 package	-	91	
		Standard WLCSP36 package	-	79	
		Thin WLCSP36 package	-	84	
		LQFP32 package	-	88	
		UFQFPN32	-	132	

Table 27. Current consumption in Run mode, code with data processing running from Flash

Symbol	Parameter	Conditions		f_{HCLK}	Typ	Max(1)	Unit
I_{DD} (Run from Flash)	Supply current in Run mode, code executed from Flash	$f_{HSE} = f_{HCLK}$ up to 16 MHz included, $f_{HSE} = f_{HCLK}/2$ above 16 MHz (PLL ON)(2)	Range 3, V_{CORE}=1.2 V VOS[1:0]=11	1 MHz	165	230	µA
				2 MHz	290	360	
				4 MHz	555	630	
			Range 2, V_{CORE}=1.5 V, VOS[1:0]=10,	4 MHz	0.665	0.74	mA
				8 MHz	1.3	1.4	
				16 MHz	2.6	2.8	
			Range 1, V_{CORE}=1.8 V, VOS[1:0]=01	8 MHz	1.55	1.7	
				16 MHz	3.1	3.4	
				32 MHz	6.3	6.8	
		MSI clock	Range 3, V_{CORE}=1.2 V, VOS[1:0]=11	65 kHz	36.5	110	µA
				524 kHz	99.5	190	
				4.2 MHz	620	700	
		HSI clock	Range 2, V_{CORE}=1.5 V, VOS[1:0]=10,	16 MHz	2.6	2.9	mA
			Range 1, V_{CORE}=1.8 V, VOS[1:0]=01	32 MHz	6.25	7	

1. Guaranteed by characterization results at 125 °C, unless otherwise specified.
2. Oscillator bypassed (HSEBYP = 1 in RCC_CR register).

Table 28. Current consumption in Run mode vs code type, code with data processing running from Flash

Symbol	Parameter	Conditions			f_{HCLK}	Typ	Unit
I_{DD} (Run from Flash)	Supply current in Run mode, code executed from Flash	$f_{HSE} = f_{HCLK}$ up to 16 MHz included, $f_{HSE} = f_{HCLK}/2$ above 16 MHz (PLL ON)(1)	Range 3, V_{CORE}=1.2 V, VOS[1:0]=11	Dhrystone	4 MHz	555	µA
				CoreMark		585	
				Fibonacci		440	
				while(1)		355	
				while(1), prefetch OFF		353	
			Range 1, V_{CORE}=1.8 V, VOS[1:0]=01	Dhrystone	32 MHz	6.3	mA
				CoreMark		6.3	
				Fibonacci		6.55	
				while(1)		5.4	
				while(1), prefetch OFF		5.2	

1. Oscillator bypassed (HSEBYP = 1 in RCC_CR register).

Table 29. Current consumption in Run mode, code with data processing running from RAM

Symbol	Parameter	Conditions		f_{HCLK}	Typ	Max(1)	Unit
I_{DD} (Run from RAM)	Supply current in Run mode, code executed from RAM, Flash switched off	f_{HSE} = f_{HCLK} up to 16 MHz included, f_{HSE} = f_{HCLK}/2 above 16 MHz (PLL ON)(2)	Range 3, V_{CORE}=1.2 V, VOS[1:0]=11	1 MHz	135	170	µA
				2 MHz	240	270	
				4 MHz	450	480	
			Range 2, V_{CORE}=1.5 ,V, VOS[1:0]=10	4 MHz	0.52	0.6	mA
				8 MHz	1	1.2	
				16 MHz	2	2.3	
			Range 1, V_{CORE}=1.8 V, VOS[1:0]=01	8 MHz	1.25	1.4	
				16 MHz	2.45	2.8	
				32 MHz	5.1	5.4	
		MSI clock	Range 3, V_{CORE}=1.2 V, VOS[1:0]=11	65 kHz	34.5	75	µA
				524 kHz	83	120	
				4.2 MHz	485	540	
		HSI16 clock source (16 MHz)	Range 2, V_{CORE}=1.5 V, VOS[1:0]=10	16 MHz	2.1	2.3	mA
			Range 1, V_{CORE}=1.8 V, VOS[1:0]=01	32 MHz	5.1	5.6	

1. Guaranteed by characterization results at 125 °C, unless otherwise specified.
2. Oscillator bypassed (HSEBYP = 1 in RCC_CR register).

Table 30. Current consumption in Run mode vs code type, code with data processing running from RAM(1)

Symbol	Parameter	Conditions			f_{HCLK}	Typ	Unit
I_{DD} (Run from RAM)	Supply current in Run mode, code executed from RAM, Flash switched off	f_{HSE} = f_{HCLK} up to 16 MHz included, f_{HSE} = f_{HCLK}/2 above 16 MHz (PLL ON)(2)	Range 3, V_{CORE}=1.2 V, VOS[1:0]=11	Dhrystone	4 MHz	450	µA
				CoreMark		575	
				Fibonacci		370	
				while(1)		340	
			Range 1, V_{CORE}=1.8 V, VOS[1:0]=01	Dhrystone	32 MHz	5.1	mA
				CoreMark		6.25	
				Fibonacci		4.4	
				while(1)		4.7	

1. Guaranteed by characterization results, unless otherwise specified.
2. Oscillator bypassed (HSEBYP = 1 in RCC_CR register).

On-chip peripheral current consumption

The current consumption of the on-chip peripherals is given in the following tables. The MCU is placed under the following conditions:

- all I/O pins are in input mode with a static value at V_{DD} or V_{SS} (no load)
- all peripherals are disabled unless otherwise mentioned
- the given value is calculated by measuring the current consumption
  - with all peripherals clocked OFF
  - with only one peripheral clocked on

Table 37. Peripheral current consumption in Run or Sleep mode(1)

Peripheral		Typical consumption, V_{DD} = 3.0 V, T_A = 25 °C				Unit
		Range 1, V_{CORE}=1.8 V VOS[1:0] = 01	Range 2, V_{CORE}=1.5 V VOS[1:0] = 10	Range 3, V_{CORE}=1.2 V VOS[1:0] = 11	Low-power sleep and run	
APB1	I2C1	11	9.5	7.5	9	µA/MHz (f_{HCLK})
	I2C2	4	3.5	3	2.5	
	LPTIM1	10	8.5	6.5	8	
	LPUART1	8	6.5	5.5	6	
	SPI2	9	4.5	3.5	4	
	USART2	14.5	12	9.5	11	
	TIM2	10.5	8.5	7	9	
	TIM6	3.5	3	2.5	2	
	WWDG	3	2	2	2	
APB2	ADC1(2)	5.5	5	3.5	4	µA/MHz (f_{HCLK})
	SPI1	4	3	3	2.5	
	USART1	14.5	11.5	9.5	12	
	TIM21	7.5	6	5	5.5	
	TIM22	7	6	5	6	
	FIREWALL	1.5	1	1	0.5	
	DBGMCU	1.5	1	1	0.5	
	SYSCFG	2.5	2	2	1.5	
Cortex-M0+ core I/O port	GPIOA	3.5	3	2.5	2.5	µA/MHz (f_{HCLK})
	GPIOB	3.5	2.5	2	2.5	
	GPIOC	8.5	6.5	5.5	7	
	GPIOD	1	0.5	0.5	0.5	
AHB	CRC	1.5	1	1	1	µA/MHz (f_{HCLK})
	FLASH	0(3)	0(3)	0(3)	0(3)	
	DMA1	10	8	6.5	8.5	

6.3.6 External clock source characteristics

High-speed external user clock generated from an external source

In bypass mode the HSE oscillator is switched off and the input pin is a standard GPIO.The external clock signal has to respect the I/O characteristics in *Section 6.3.12*. However, the recommended clock input waveform is shown in *Figure 19*.

Table 40. High-speed external user clock characteristics(1)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
f_{HSE_ext}	User external clock source frequency	CSS is ON or PLL is used	1	8	32	MHz
		CSS is OFF, PLL not used	0	8	32	MHz
V_{HSEH}	OSC_IN input pin high level voltage	-	$0.7V_{DD}$	-	V_{DD}	V
V_{HSEL}	OSC_IN input pin low level voltage		V_{SS}	-	$0.3V_{DD}$	
$t_{w(HSE)}$ $t_{w(HSE)}$	OSC_IN high or low time		12	-	-	ns
$t_{r(HSE)}$ $t_{f(HSE)}$	OSC_IN rise or fall time		-	-	20	
$C_{in(HSE)}$	OSC_IN input capacitance		-	2.6	-	pF
$DuCy_{(HSE)}$	Duty cycle		45	-	55	%
I_L	OSC_IN Input leakage current	$V_{SS} \leq V_{IN} \leq V_{DD}$	-	-	±1	µA

1. Guaranteed by design.

Figure 19. High-speed external clock source AC timing diagram

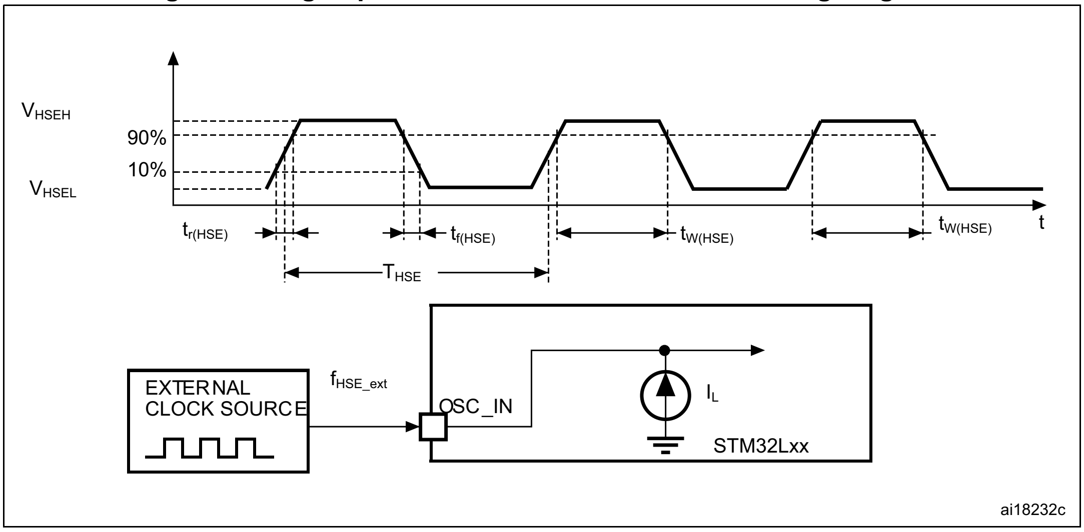


Table 49. Flash memory and data EEPROM characteristics

Symbol	Parameter	Conditions	Min	Typ	Max(1)	Unit
I_{DD}	Average current during the whole programming / erase operation	T_A = 25 °C, V_{DD} = 3.6 V	-	500	700	µA
	Maximum current (peak) during the whole programming / erase operation		-	1.5	2.5	mA

1. Guaranteed by design.

Table 50. Flash memory and data EEPROM endurance and retention

Symbol	Parameter	Conditions	Value Min(1)	Unit
N_{CYC}(2)	Cycling (erase / write) Program memory	T_A = -40°C to 105 °C	10	kcycles
	Cycling (erase / write) EEPROM data memory		100	
	Cycling (erase / write) Program memory	T_A = -40°C to 125 °C	0.2	
	Cycling (erase / write) EEPROM data memory		2	
t_{RET}(2)	Data retention (program memory) after 10 kcycles at T_A = 85 °C	T_{RET} = +85 °C	30	years
	Data retention (EEPROM data memory) after 100 kcycles at T_A = 85 °C		30	
	Data retention (program memory) after 10 kcycles at T_A = 105 °C	T_{RET} = +105 °C	10	
	Data retention (EEPROM data memory) after 100 kcycles at T_A = 105 °C			
	Data retention (program memory) after 200 cycles at T_A = 125 °C	T_{RET} = +125 °C		
	Data retention (EEPROM data memory) after 2 kcycles at T_A = 125 °C			

1. Guaranteed by characterization results.
2. Characterization is done according to JEDEC JESD22-A117.

6.3.11 Electrical sensitivity characteristics

Based on three different tests (ESD, LU) using specific measurement methods, the device is stressed in order to determine its performance in terms of electrical sensitivity.

Electrostatic discharge (ESD)

Electrostatic discharges (a positive then a negative pulse separated by 1 second) are applied to the pins of each sample according to each pin combination. The sample size depends on the number of supply pins in the device (3 parts × (n+1) supply pins). This test conforms to the ANSI/JEDEC standard.

Table 53. ESD absolute maximum ratings

Symbol	Ratings	Conditions	Class	Maximum value(1)	Unit
$V_{ESD(HBM)}$	Electrostatic discharge voltage (human body model)	T_A = +25 °C, conforming to ANSI/JEDEC JS-001	2	2000	V
$V_{ESD(CDM)}$	Electrostatic discharge voltage (charge device model)	T_A = +25 °C, conforming to ANSI/ESD STM5.3.1.	C4	500	

1. Guaranteed by characterization results.

Static latch-up

Two complementary static tests are required on six parts to assess the latch-up performance:

- A supply overvoltage is applied to each power supply pin
- A current injection is applied to each input, output and configurable I/O pin

These tests are compliant with EIA/JESD 78A IC latch-up standard.

Table 54. Electrical sensitivities

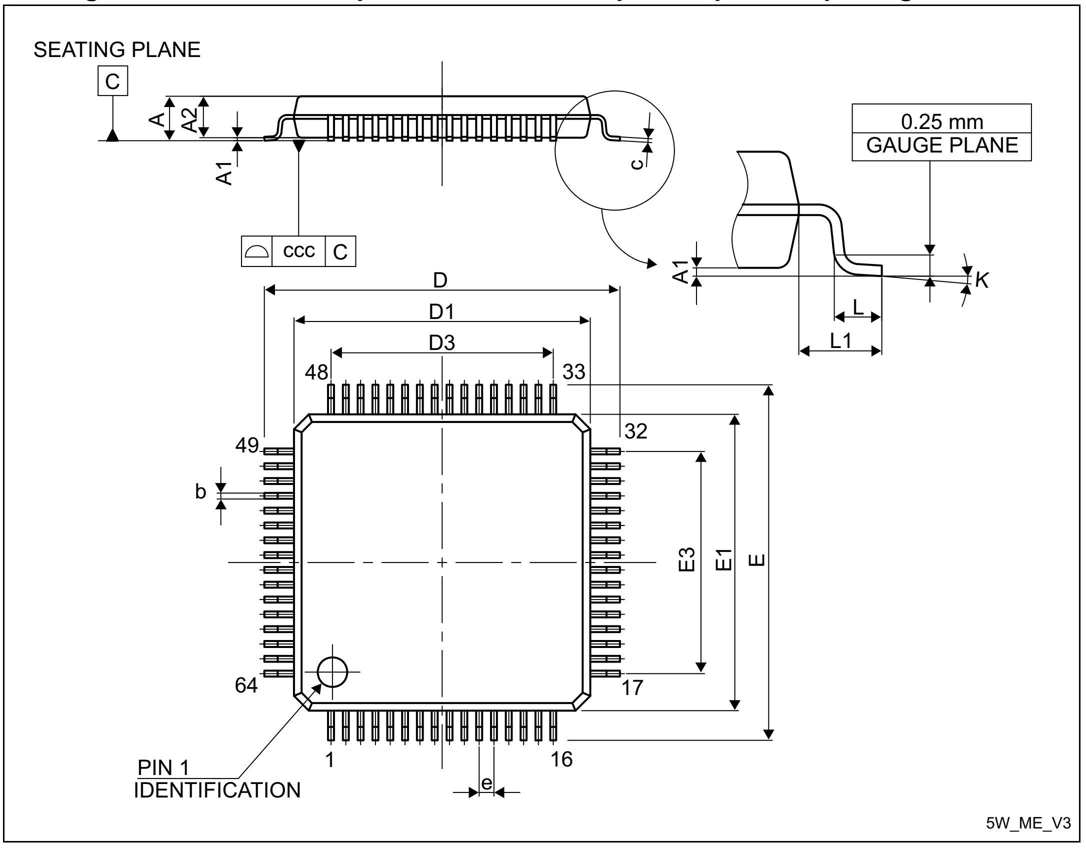
Symbol	Parameter	Conditions	Class
LU	Static latch-up class	T_A = +125 °C conforming to JESD78A	II level A

7 Package information

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK® packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status *are available at www.st.com.* ECOPACK® is an ST trademark.

7.1 LQFP64 package information

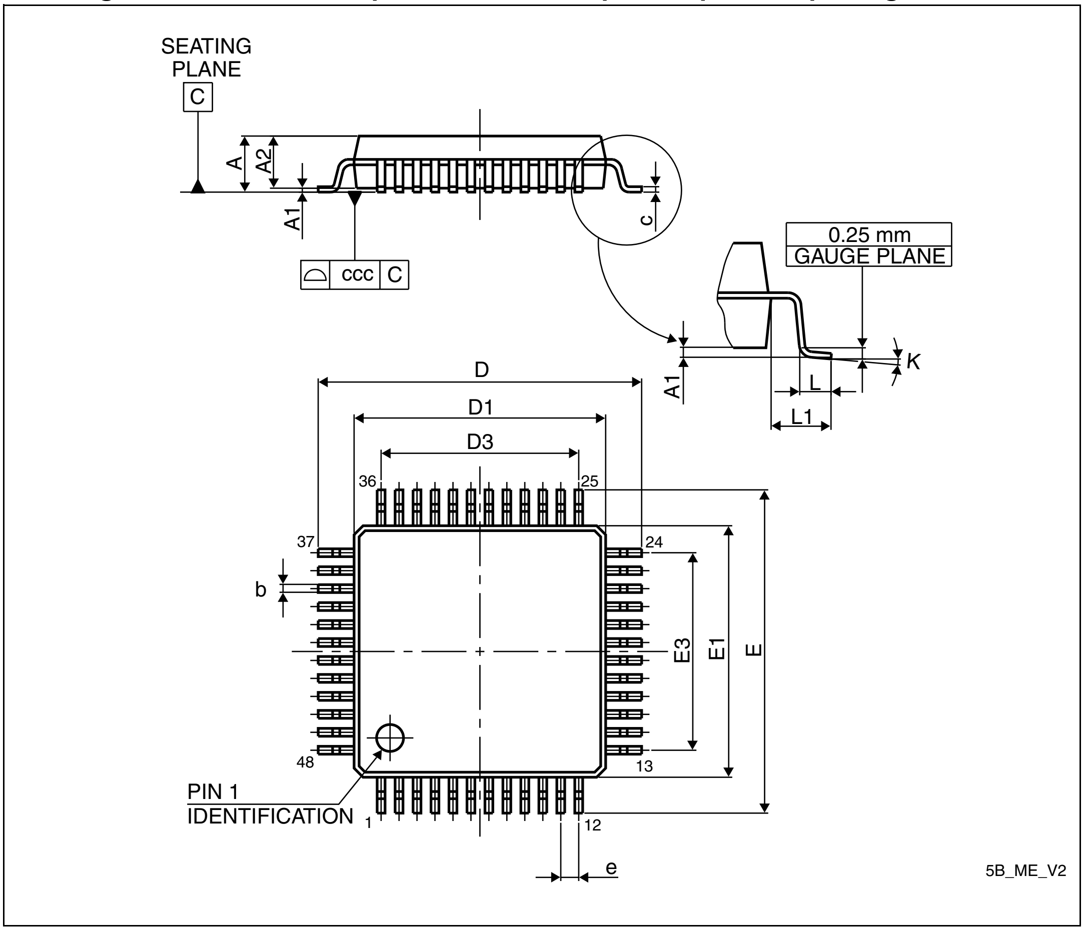
Figure 37. LQFP64 - 64-pin, 10 x 10 mm low-profile quad flat package outline



1. Drawing is not to scale.

7.3 LQFP48 package information

Figure 43. LQFP48 - 48-pin, 7 x 7 mm low-profile quad flat package outline



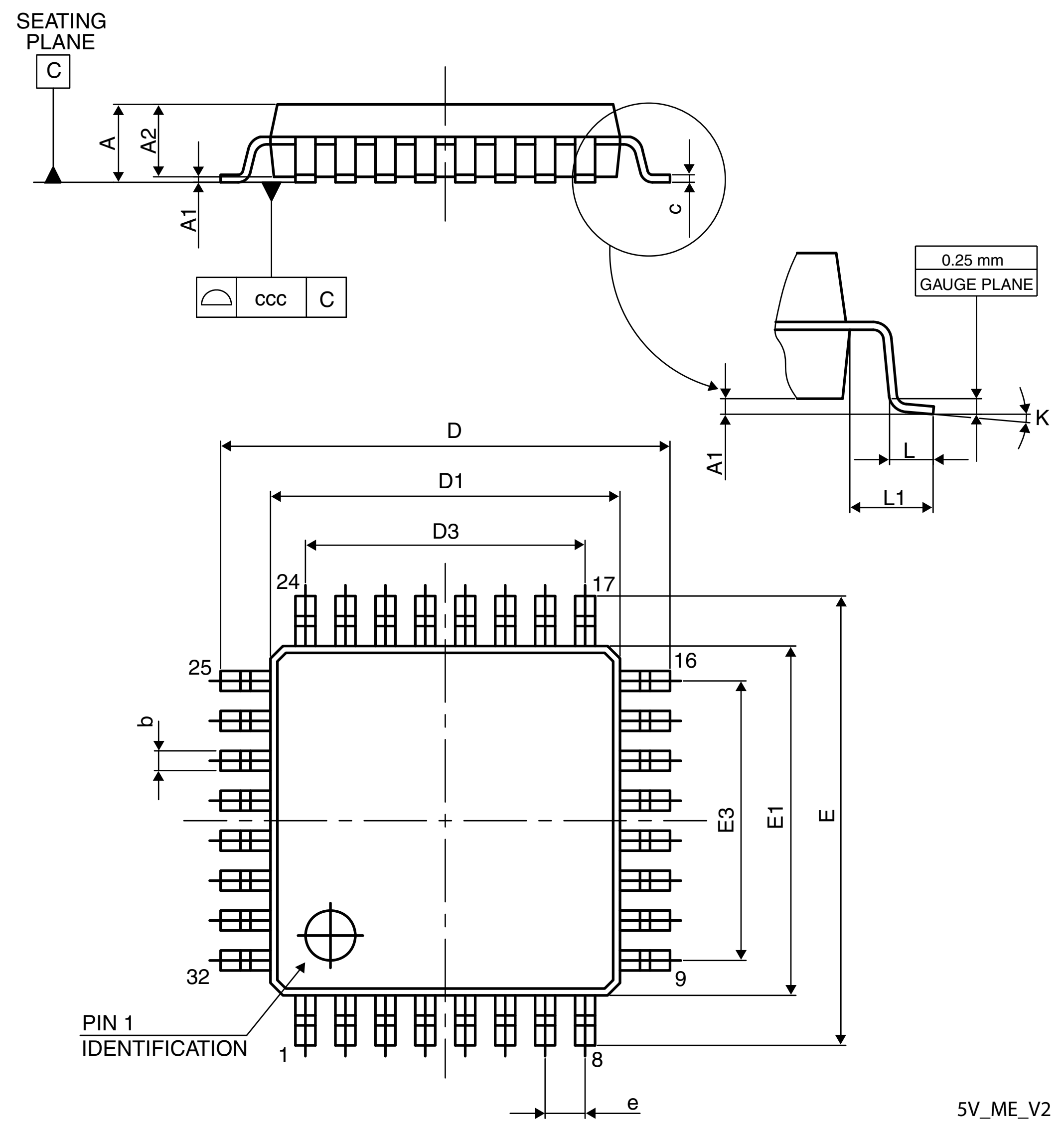
1. Drawing is not to scale.

Table 81. WLCSP36 recommended PCB design rules

Dimension	Recommended values
Pitch	0.4 mm
Dpad	260 µm max. (circular) 220 µm recommended
Dsm	300 µm min. (for 260 µm diameter pad)
PCB pad design	Non-solder mask defined via underbump allowed

7.6 LQFP32 package information

Figure 51. LQFP32 - 32-pin, 7 x 7 mm low-profile quad flat package outline



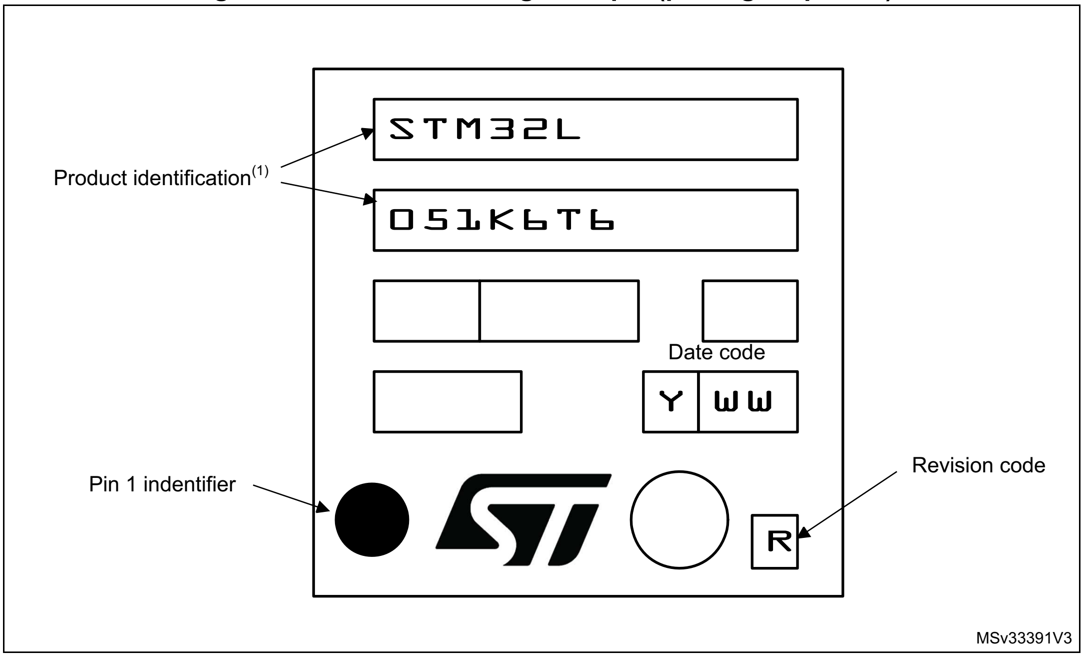
1. Drawing is not to scale.

Device marking for LQFP32

The following figure gives an example of topside marking versus pin 1 position identifier location.

Other optional marking or inset/upset marks, which depend on supply chain operations, are not indicated below.

Figure 53. LQFP32 marking example (package top view)



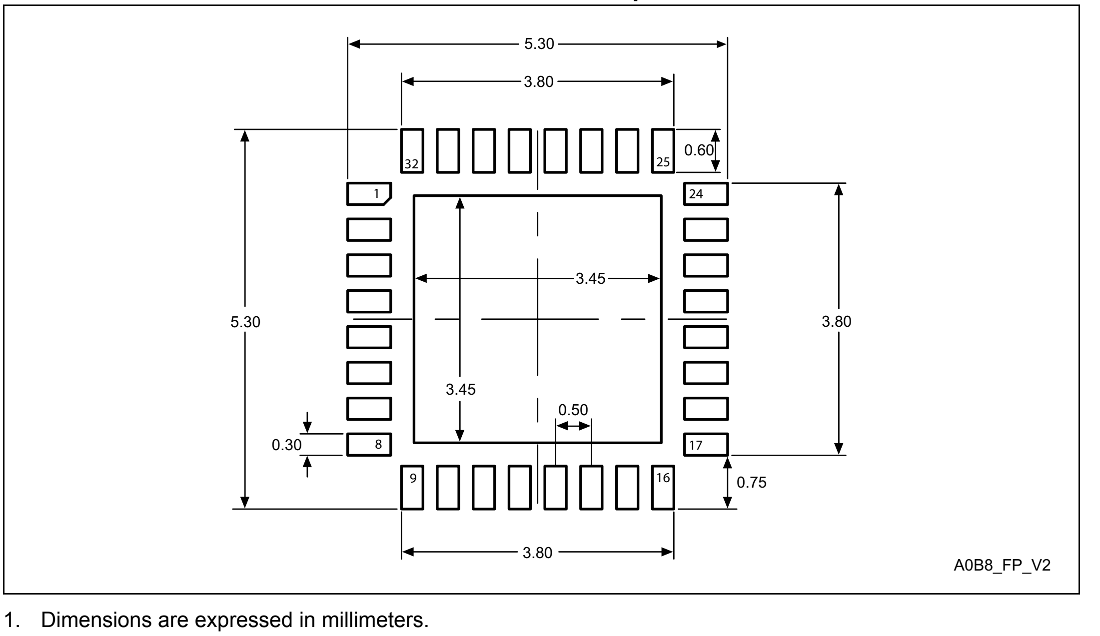
1. Parts marked as “ES”, “E” or accompanied by an Engineering Sample notification letter, are not yet qualified and therefore not yet ready to be used in production and any consequences deriving from such usage will not be at ST charge. In no event, ST will be liable for any customer usage of these engineering samples in production. ST Quality has to be contacted prior to any decision to use these Engineering samples to run qualification activity.

Table 83. UFQFPN32 - 32-pin, 5x5 mm, 0.5 mm pitch ultra thin fine pitch quad flat package mechanical data

Symbol	millimeters			inches(1)		
	Min	Typ	Max	Min	Typ	Max
A	0.500	0.550	0.600	0.0197	0.0217	0.0236
A1	0.000	0.020	0.050	0.0000	0.0008	0.0020
A3	-	0.152	-	-	0.0060	-
b	0.180	0.230	0.280	0.0071	0.0091	0.0110
D	4.900	5.000	5.100	0.1929	0.1969	0.2008
D1	3.400	3.500	3.600	0.1339	0.1378	0.1417
D2	3.400	3.500	3.600	0.1339	0.1378	0.1417
E	4.900	5.000	5.100	0.1929	0.1969	0.2008
E1	3.400	3.500	3.600	0.1339	0.1378	0.1417
E2	3.400	3.500	3.600	0.1339	0.1378	0.1417
e	-	0.500	-	-	0.0197	-
L	0.300	0.400	0.500	0.0118	0.0157	0.0197
ddd	-	-	0.080	-	-	0.0031

1. Values in inches are converted from mm and rounded to 4 decimal digits.

Figure 55. UFQFPN32 - 32-pin, 5x5 mm, 0.5 mm pitch ultra thin fine pitch quad flat recommended footprint



1. Dimensions are expressed in millimeters.